

2021 Silicon Nanoelectronics Workshop

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Sunday, June 13, 2021

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Toshifumi Irisawa, *AIST*

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The University of Tokyo
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CEA-INAC

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1. TSMC (Taiwan)
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° Jens Trommer², Maciej Wiatr¹
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1. *Institute of Microelectronics, Chinese Academy of Sciences (China)*, 2. *University of Chinese Academy of Sciences (China)*

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1. *Sandia National Labs. (United States of America)*

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1. Fraunhofer IPMS-Center Nanoelectronics Technologies (Germany), 2. Institut für Angewandte Physik, Technische Universität Dresden, (Germany)
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1. State Key Laboratory of ASIC and System, Fudan Univ. (China), 2. Hefei Reliance Memory Ltd. (China)
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1. Department of Electrical and Computer Engineering (ECE), Seoul National Univ. (Korea)

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Session Chair: Toshifumi Irisawa, AIST

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1. imec (Belgium)
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1. National Institute of Advanced Industrial Science and Technology (AIST) (Japan)
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1. Univ. of Granada (Spain), 2. Advanced Microelectronic Center Aachen (AMICA), AMO GmbH (Germany), 3. RWTH Aachen Univ. (Germany)

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1. RWTH Aachen University (Germany), 2. University of Siegen (Germany), 3. AMO GmbH (Germany), 4. National Research Council (CNR) (Italy)
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1. RWTH Aachen Univ. (Germany), 2. AMO GmbH (Germany)
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1. AMO GmbH (Germany), 2. Chair of Electronics Devices, RWTH Aachen Univ. (Germany), 3. Compound Semiconductor Tech., RWTH Aachen Univ. (Germany), 4. AIXTRON SE (Germany)

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Session Chair: Katsuhiko Nishiguchi, NTT Basic Res. Lab.

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1. Grad. Sch. of Sci. and Tech., Shizuoka Univ. (Japan), 2. Fac. of Eng., Shizuoka Univ. (Japan), 3. Res. Inst. of Elec., Shizuoka Univ. (Japan)
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1. Grad. Sch. of Sci. and Tech., Shizuoka Univ. (Japan), 2. Res. Inst. of Elec., Shizuoka Univ. (Japan)

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1. Yokohama Nat'l Univ. (Japan)